

Atklāta un izpētīta augsta spiediena fāžu pāreja izolators-metāls alvas volframātā

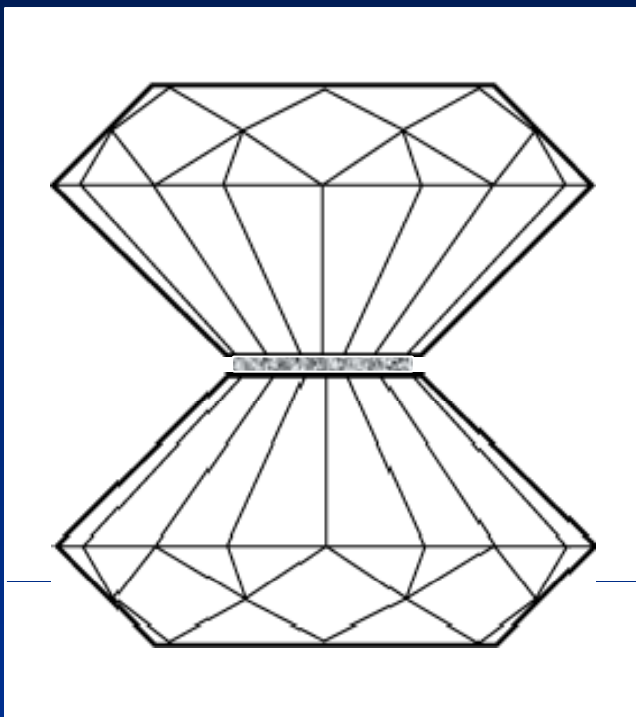
Sasniegumi teorētiskajā zinātnē

LZA akadēmiķis Aleksejs Kuzmins, *Dr.phys.* Andris Anspoks,
Dr.phys. Aleksandrs Kalinko, *Dr.phys.* Jānis Timošenko,
Dr.phys. Roberts Kalendarevs

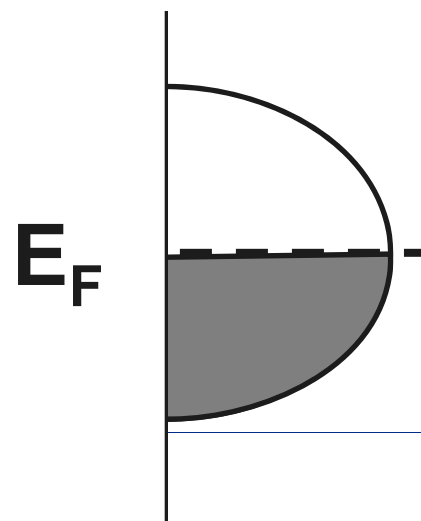


LATVIJAS UNIVERSITĀTES
CIETVIELU FIZIKAS INSTITŪTS

Fāžu pāreja izolators-metāls

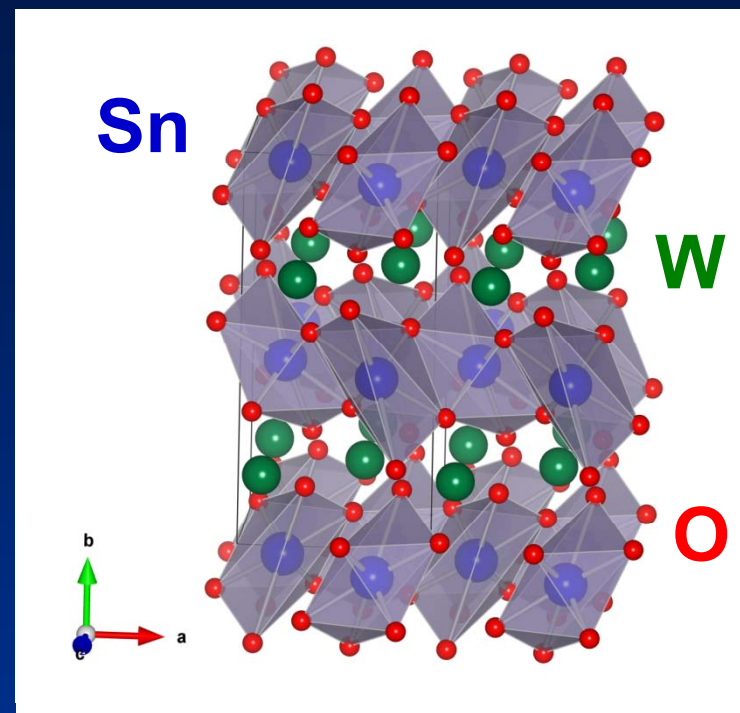
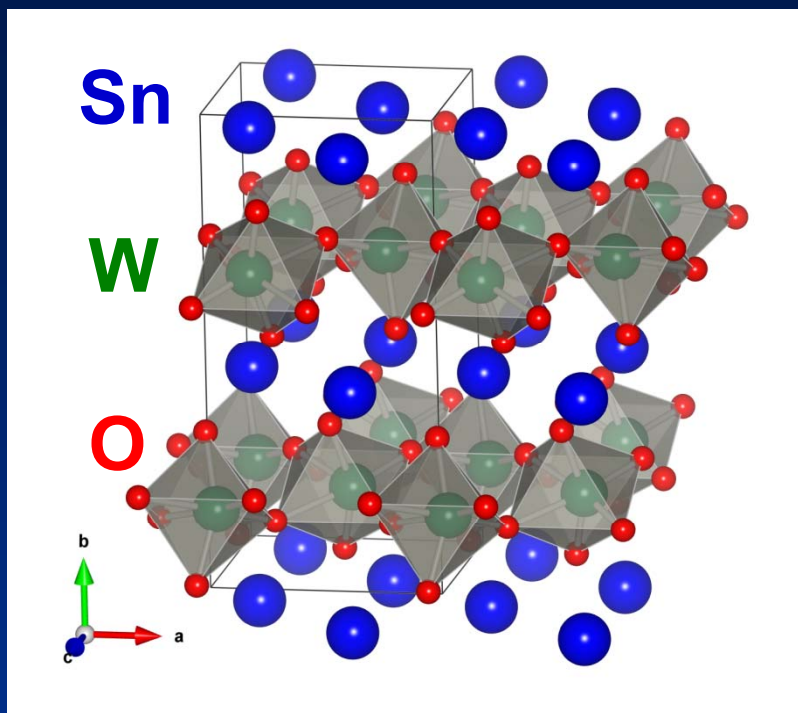


metāls



**Pietiekami augstā spiedienā
visas vielas pāriet metāliskā stāvoklī!**

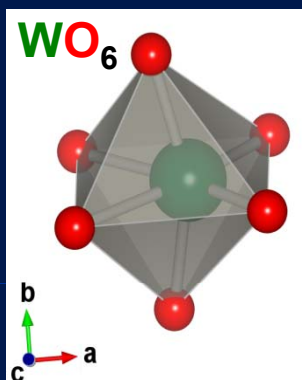
Alvas volframāta (α -SnWO₄) kristalogrāfiskā struktūra



Pamata struktūrvienības:

**WO₆ oktaedri
ar no centra
nobīdītu W**

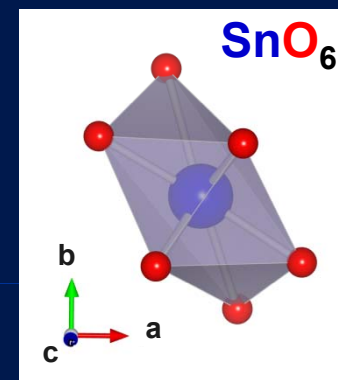
$$\begin{aligned} 2 \times R(\text{W-O}) &= 1.80 \text{ \AA} \\ 2 \times R(\text{W-O}) &= 1.89 \text{ \AA} \\ 2 \times R(\text{W-O}) &= 2.14 \text{ \AA} \end{aligned}$$



+

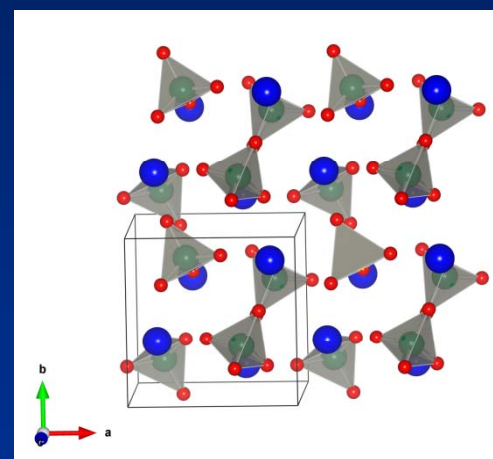
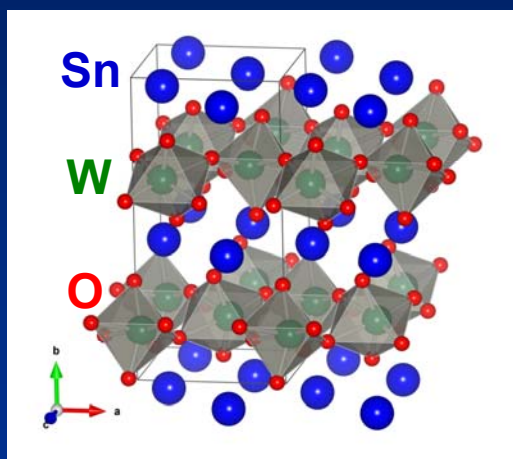
**stipri izkropļoti
SnO₆ oktaedri**

$$\begin{aligned} 2 \times R(\text{Sn-O}) &= 2.18 \text{ \AA} \\ 2 \times R(\text{Sn-O}) &= 2.39 \text{ \AA} \\ 2 \times R(\text{Sn-O}) &= 2.83 \text{ \AA} \end{aligned}$$



Alvas volframāta (α -SnWO₄) īpašības

- Ortorombiskā slāņaina struktūra (*Pnna*, no. 52)
- Aizliegtā zona $E_g \approx 1.7$ eV
- Fāžu pāreja α -SnWO₄ $\xrightarrow{650^\circ\text{C}}$ β -SnWO₄



kubisks (*P2₁3*, no. 198), $E_g \approx 2.6$ eV

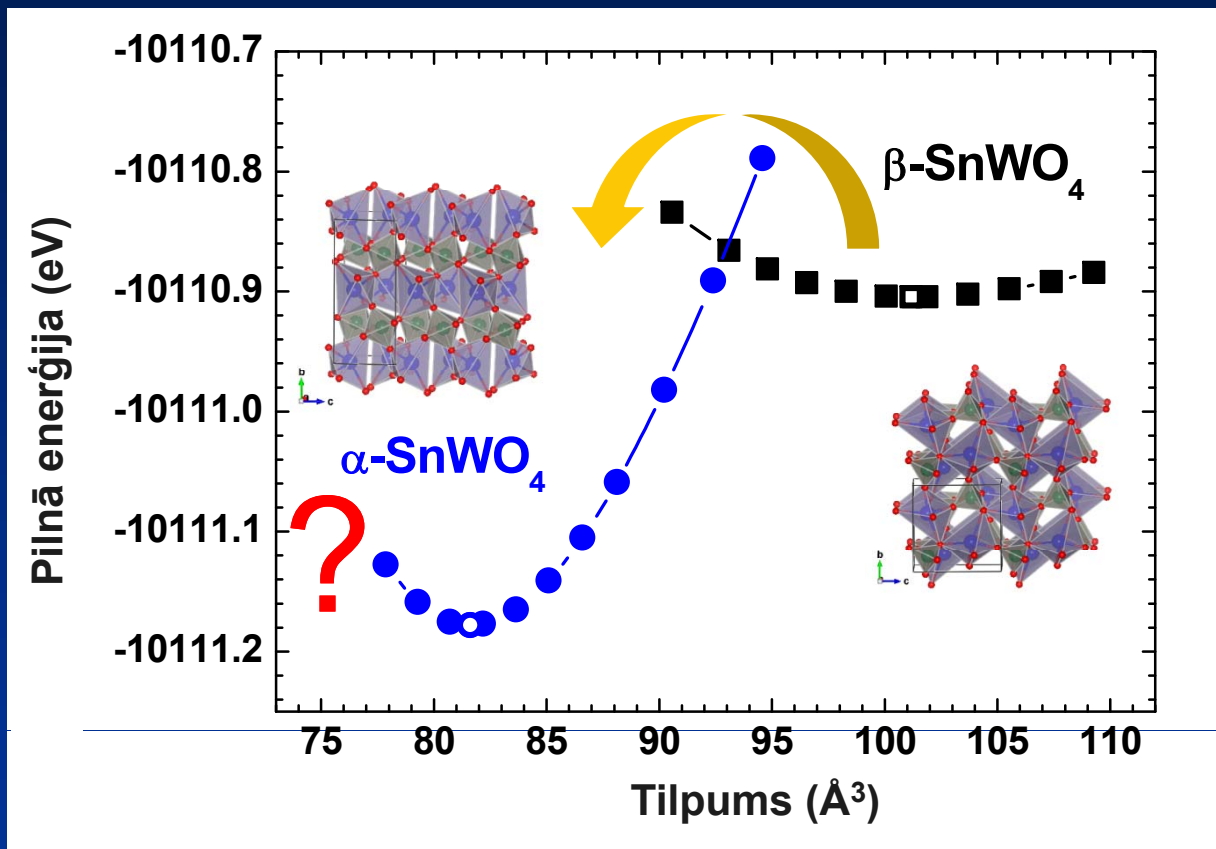
Kas notiek zem augsta spiediena?





Teorētiskās modelēšanas rezultāti

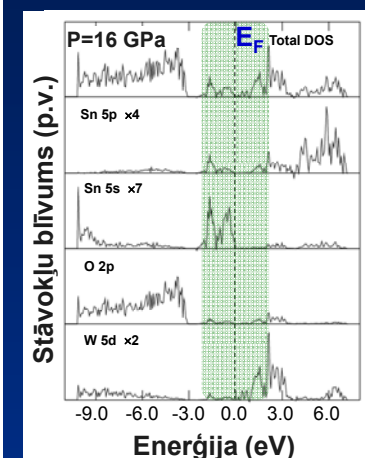
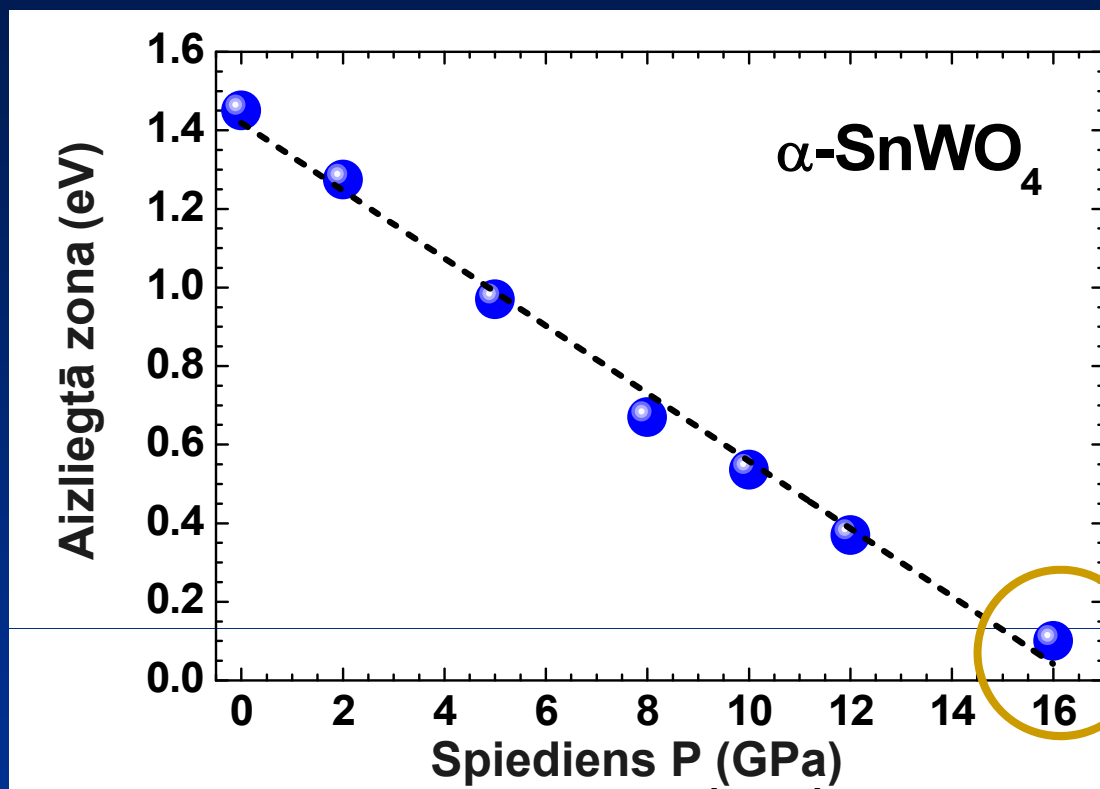
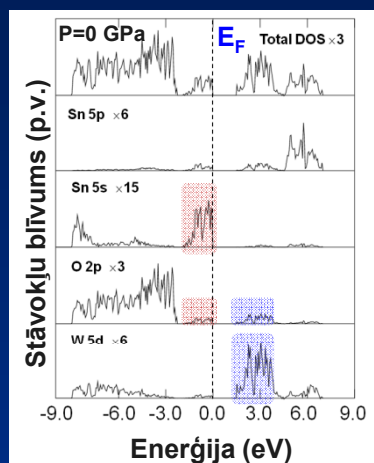
Lielāks spiediens – mazāks tilpums



Kas notiek zem augsta spiediena ar α -SnWO₄?



Teorētiskās modelēšanas rezultāti



Notiek fāžu pāreja vadošā stāvoklī!

Kāpēc?



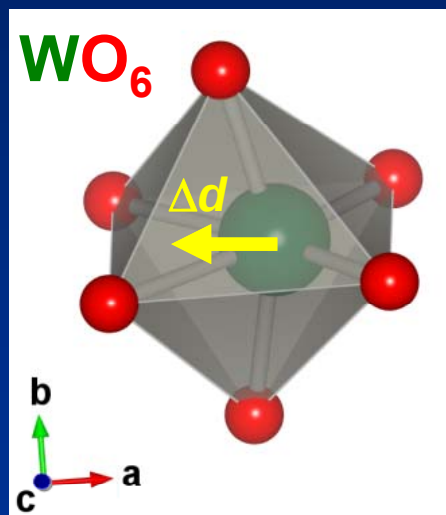


Teorētiskās modelēšanas rezultāti

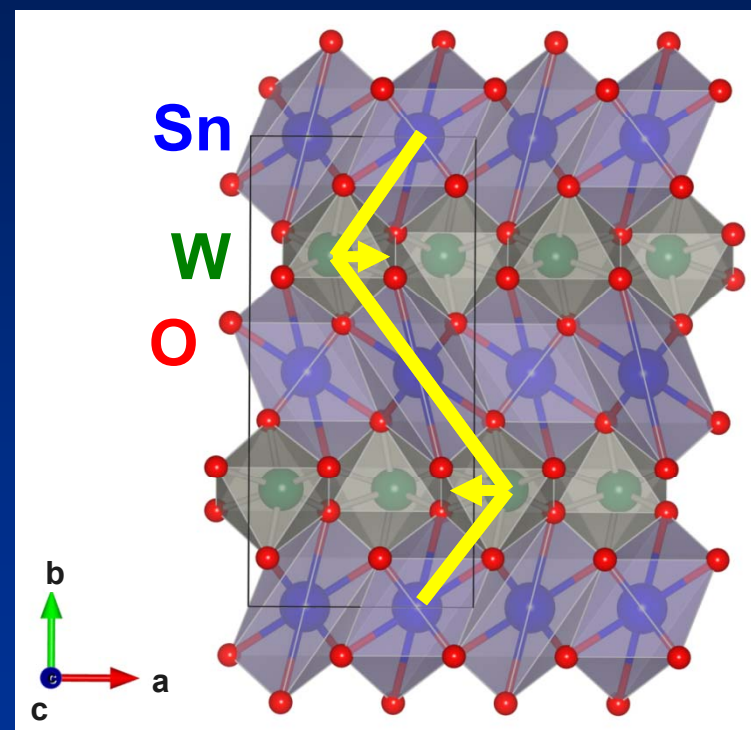
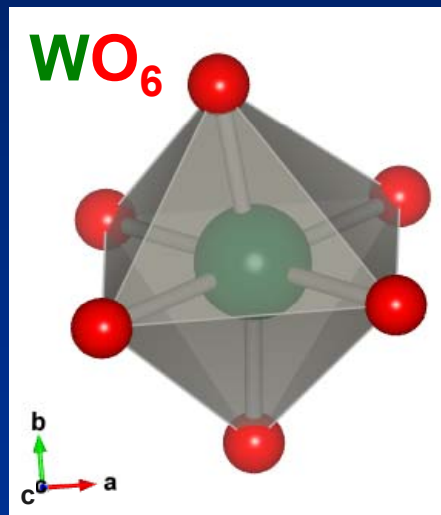
Elektronu delokalizācija
b-ass virzienā

Volframa nobīde

$$\Delta d \sim 0.2 \text{ \AA}$$



Oktaedra
simetrizācija



1

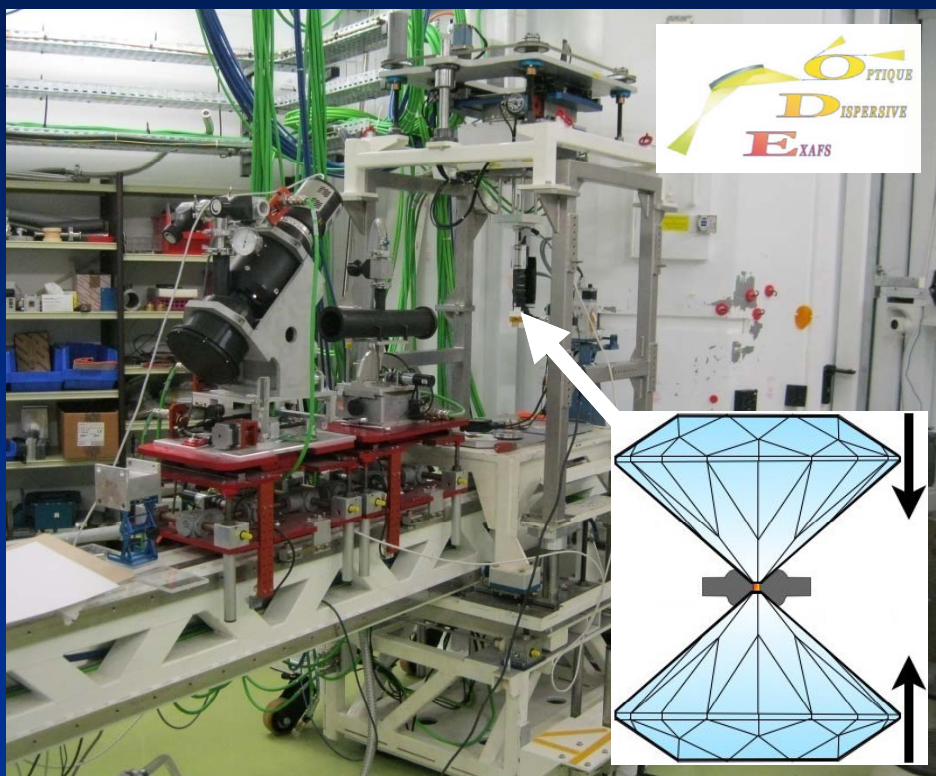
2

3



***In-situ* eksperimenti SOLEIL sinhrotrona centrā**

Rentgenabsorbcijas spektroskopija



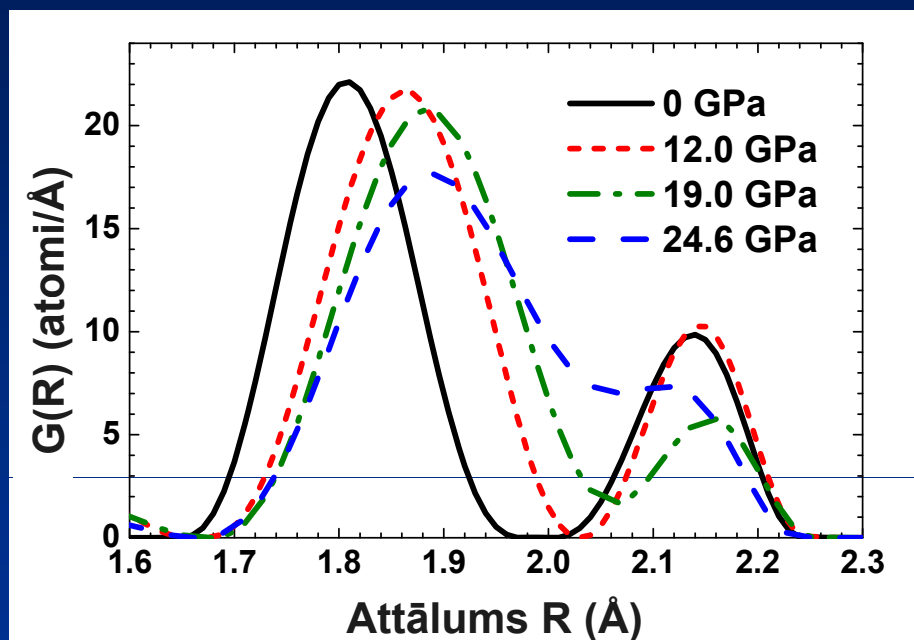
Infrasarkanā spektroskopija



Spiediens $P = 0 - 25$ GPa (0 - 250 000 atm)

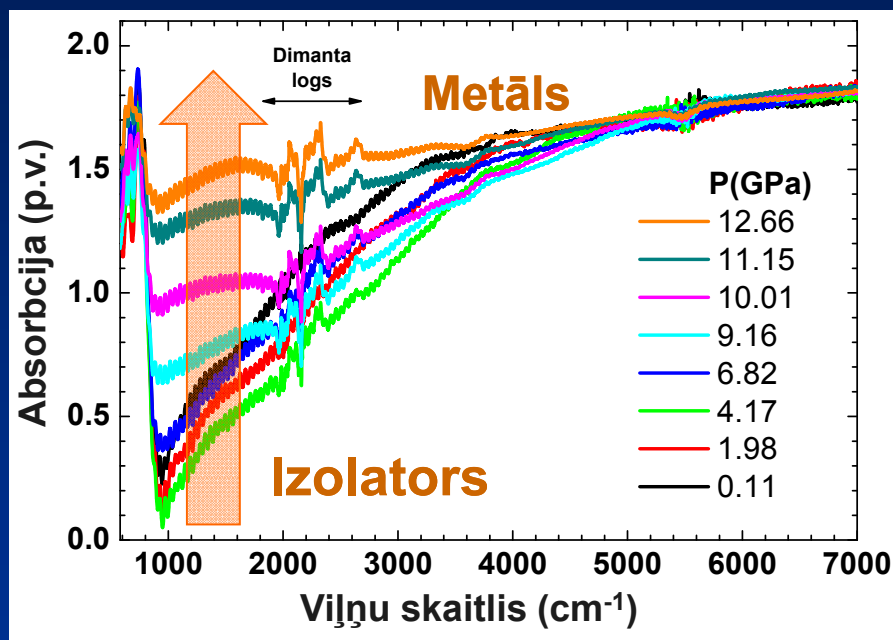
Galvenie eksperimentālie rezultāti

WO₆ oktaedra simetrizācija



1

Aizliegtās zonas kolapss infrasarkanā diapazonā



2

Sakrīt ar teoriju!



External pressure and composition effects on the atomic and electronic structure of SnWO_4

A. Kuzmin^{a,*}, A. Anspoks^a, A. Kalinko^b, J. Timoshenko^a, R. Kalendarev^a

^aInstitute of Solid State Physics, University of Latvia, Kr. J. B. 1063 Riga, Latvia
^bSynchrotron SOLEIL, Orme des Merisiers, Saint-Aubin, BP 48, 91192 Gif-sur-Yvette, France

ARTICLE INFO

Article history:
Received 14 July 2014
Received in revised form
25 November 2014
Accepted 1 December 2014
Available online 18 December 2014

Keywords:
Tin tungstate
First-principles calculation
Insulator-to-metal transition
EXAFS

Contents lists available at ScienceDirect
Solar Energy Materials & Solar Cells
journal homepage: www.elsevier.com/locate/solmat

ABSTRACT

The atomic and electronic structure of tin tungstate (SnWO_4) in the α - and β -phases was studied by the W atomic orbital (AO) Hartree-Fock (HF) distorted WO_4 octahedra. In addition, there are distortions in the α - SnWO_4 and compressibility of β - SnWO_4 to metal transition symmetrization of and closing of band

TOP Publishing | Royal Swedish Academy of Sciences
Phys. Scr. 89 (2015) 044005 (9pp)

High-pressure x-ray absorption spectroscopy study of tin tungstates

A. Kuzmin^a, A. Anspoks^a, A. Kalinko^b, J. Timoshenko^a, R. Kalendarev^a,
L. Nataf^c, F. Baudalet^c and T. Irifune^d

^aInstitute of Solid State Physics, University of Latvia, Kr. J. B. 1063 Riga, Latvia
^bSynchrotron SOLEIL, Orme des Merisiers, Saint-Aubin, BP 48, 91192 Gif-sur-Yvette, France
^cGeodynamics Research Center, Ehime University, 2-5 Bunkyo-cho, Matsuyama, Ehime 790-8577, Japan

E-mail: a.kuzmin@cfi.lv

Received 28 September 2014
Accepted for publication 30 December 2014
Published 13 August 2015

Abstract

Room-temperature pressure-dependent (0–25 GPa) x-ray absorption spectroscopy at the $W_{L_{2,3}}$ -edges of α - SnWO_4 and β - SnWO_4 was performed using a dispersive setup and a high-pressure nondiamond anvil cell. The detailed analysis of experimental x-ray absorption near-edge structure and extended x-ray absorption fine structure data suggests that upon increasing pressure, a displacement of tungsten atoms by about 0.2 Å toward the center of the WO_4 octahedra occurs in α - SnWO_4 , whereas the coordination of tungsten atoms changes from tetrahedral to distorted octahedral in β - SnWO_4 .

Keywords: tin tungstate, high-pressure, EXAFS, XANES, $W_{L_{2,3}}$ -edges

1. Introduction

Tin tungstate (SnWO_4) has two polymorphs: the low-temperature orthorhombic α -phase [1] and the high-temperature cubic β -phase [2]. The reversible phase transition is controlled by a diffusion process that occurs at $\sim 670^\circ\text{C}$ [1, 2]. Note that high-temperature β - SnWO_4 can be produced at room temperature by rapid cooling, so that both the α and β phases can be studied at the same temperature and pressure.

The crystal structures of the two tungstates differ significantly, although both are composed of metal-oxygen polyhedra. Distorted WO_4 and SnO_4 octahedra are the building blocks of α - SnWO_4 , whereas slightly deformed WO_4 tetrahedral and strongly distorted SnO_4 octahedral units form the β - SnWO_4 structure. The distortion of SnO_4 octahedra is caused by a stereochemically active $5s^2$ lone electron pair via the second-order Jahn-Teller (SOJT) effect [3–5]. The SOJT effect also causes a distortion of WO_4 octahedra due to the partially covalent W–O bonding and W^{6+} ($5d^0$) electronic configuration [5, 6].

Metal-oxygen interactions are responsible for the electronic structure of tin tungstates. The results of first-principles calculations [4, 5] indicate that the valence band of both tungstates is formed by strongly interacting O 2p and Sn 5s states, whereas the conduction band originates from W 5d- d

2p antibonding states with some admixture of Sn 5p states. The band gaps are rather small: indirect 1.7 eV [4] (1.45 eV [5]) in α - SnWO_4 and direct 2.6–2.7 eV [1, 4, 7] (4.36 eV [5]) in β - SnWO_4 . Therefore, they can be affected by the application of external pressure. The results of our recent first-principles calculations [8] suggest a band gap shrinkage under the isothermal pressure of about 16 GPa in α - SnWO_4 , leading to the insulator-to-metal transition, whereas no such effect was found in β - SnWO_4 . Note that the pressure dependence of the electronic structure is accompanied by a change in the metal-oxygen polyhedra distortion due to both charge transfer effects and unit-cell volume reduction [8]. As a result, the pressure-induced phase transition from β - SnWO_4 to α - SnWO_4 is expected at room temperature and at a theoretical pressure of about 2 GPa (figure 1).

In this study we used x-ray absorption spectroscopy (XAS) at the $W_{L_{2,3}}$ -edges to probe the local environment in α - SnWO_4 and β - SnWO_4 up to a pressure of 25 GPa. XAS is well suited to follow local structure deformations under high pressure due to its local order sensitivity and element selectivity, as well as its ability to perform *in situ* experiments using diamond anvil cells (DACs) [9, 10]. Our previous XAS study allowed us to follow in detail the distortion of tungsten-oxygen polyhedra in a SnWO_4 tungstate up to 30 GPa [11]. However, the use of conventional single-crystal DACs

16th International Conference on X-ray Absorption Fine Structure (XAFS16)
Journal of Physics: Conference Series 712 (2016) 012122 doi:10.1088/1742-6596/712/1/012122

Pressure-induced insulator-to-metal transition in α - SnWO_4

Alexei Kuzmin^a, Andrie Anspoks^a, Aleksandr Kalinko^{b,c}, Janis Timoshenko^a, Robert Kalendarev^a, Lucie Nataf^d, François Baudalet^d,
Tetsuo Irifune^e, Pascale Roy^f

^aInstitute of Solid State Physics, University of Latvia, Riga, LV-1063 Riga, Latvia
^bUniversity of Paderborn, Faculty of Sciences, Department of
^cDESY Photon Science, Hamburg, Germany
^dSynchrotron SOLEIL, Orme des Merisiers, Saint-Aubin, BP 48, 91192 Gif-sur-Yvette, France
^eGeodynamics Research Center, Ehime University, Matsuyama

E-mail: a.kuzmin@cfi.lv

Abstract. In situ high-pressure $W_{L_{2,3}}$ and $L_{2,3}$ edge x-ray spectroscopies complemented by first-principles calculations a pressure-induced insulator-to-metal transition in α - SnWO_4 in the range of a symmetrization of metal-oxygen octahedra due to a strong O 2p states along the b-axis direction, leading to a collapse of

1. Introduction

Metal-insulator transitions in oxides are of considerable interest at century [1, 2, 3]. The phenomenon finds applications in novel electrics stimulating the discovery of new functional materials [4, 5]. An overview of recent experimental and theoretical findings on novel metal transition in low-temperature α -phase of tin tungstate (α - SnWO_4)

Tin tungstate has two polymorphs, the low-temperature orthorhombic α -phase [1] and high-temperature cubic β -phase (space group $P2_1$) into each other by a diffusion-controlled phase transition mechanism two phases have narrow band gaps ($E_g \sim 1.7$ eV in α - SnWO_4 and unique band structures, strongly influenced by the charge transfer) and tungsten atoms and the presence of the lone pair of Sn 5s electron

The crystal structure of α - SnWO_4 (Fig. 1) is composed of two octahedra, separated by layers of Sn^{2+} ions, which are also six-fold α [6]. The WO_4 octahedra within a sheet are joined by four vertices, I layer, and are distorted due to the second-order Jahn-Teller (SOJT) W^{6+} ($5d^0$) electronic configuration. This distortion is associated with W^{6+} ions in the direction of the octahedron edge, so that the bonds. The six-fold coordination of Sn^{2+} ($5s^2 5p^0$) ions is distorted three different Sn–O bonds. The pair of stereochemically active Sn for the lone pair distortion of the SnO_4 octahedron via the SOJT effect

Content from this work may be used under the terms of the Creative Commons Attribution 4.0 International license, which permits unrestricted use, distribution, and reproduction in any medium, provided the original work is properly cited. Published under license by IOP Publishing Ltd

TOP Publishing | Royal Swedish Academy of Sciences
Phys. Scr. 89 (2014) 044005 (9pp)

Extended x-ray absorption fine structure spectroscopy and first-principles study of SnWO_4

A. Kuzmin^a, A. Anspoks^a, A. Kalinko^{b,c}, J. Timoshenko^a and R. Kalendarev^a

^aInstitute of Solid State Physics, University of Latvia, Kr. J. B. 1063 Riga, Latvia
^bSynchrotron SOLEIL, Orme des Merisiers, Saint-Aubin, BP 48, 91192 Gif-sur-Yvette, France

E-mail: a.kuzmin@cfi.lv

Received 6 June 2013, revised 26 September 2013
Accepted for publication 30 September 2013
Published 25 February 2014

Abstract

The local atomic structure in α - and β - SnWO_4 was studied by synchrotron radiation $W_{L_{2,3}}$ -edge x-ray absorption spectroscopy at 10 and 300 K. Strongly distorted WO_4 octahedra were found in α - SnWO_4 , whereas nearly regular WO_4 tetrahedra were observed in β - SnWO_4 , confirming previous results. The structural results obtained were supported by the first-principles calculations, suggesting that the second-order Jahn-Teller effect is responsible for octahedral distortion.

Keywords: tin tungstate, EXAFS, $W_{L_{2,3}}$ -edge, *ab initio* calculation, Jahn-Teller effect

(Some figures may appear in colour only in the online journal)

1. Introduction

Tin tungstate (SnWO_4) is an interesting compound, which has rarely been studied. It has two polymorphs (figure 1): the low-temperature orthorhombic α -phase (space group $Pnna$, no. 52) [1] and the high-temperature cubic β -phase (space group $P2_1$, no. 198) [2]. A diffusion-controlled phase transition occurs at 670°C [2]; metastable (at room temperature) β - SnWO_4 can be prepared by a rapid quenching from above 670°C [3]. The crystal structure of orthorhombic α - SnWO_4 [1] is composed of two-dimensional (2D) sheets of WO_4 octahedra, separated by layers of Sn^{2+} ions, which are six-fold coordinated by oxygens. The WO_4 octahedra within a sheet are joined by four corners and are distorted due to the second-order Jahn-Teller (SOJT) effect [4] because of the W^{6+} ($5d^0$) electronic configuration. This distortion is associated with an off-center displacement of W^{6+} ions in the direction of the octahedron edge, so that there are three distinct W–O bonds ($2 \times 1.802, 2 \times 1.889, 2 \times 2.141$ Å). The six-fold coordination of Sn^{2+} ($5s^2 5p^0$) ions is distorted even more, leading to three different Sn–O bonds ($2 \times 2.184, 2 \times 2.392, 2 \times 2.826$ Å). The pair of stereochemically active Sn 5s electrons is responsible for the ‘lone pair’ distortion of the SnO_4 octahedron via the SOJT effect [5].

The structure of cubic β - SnWO_4 is built up of slightly deformed WO_4 tetrahedra, which are interconnected with

SnO_4 octahedra. The latter are strongly distorted via the SOJT effect [6] and have two different Sn–O bonds (3×2.214 and 3×2.810 Å) [2]. The WO_4 tetrahedra have three shorter (1.747 Å) and one longer (1.764 Å) W–O bonds; the bond length depends on how many tin atoms are bound to the oxygen atom. The distant oxygen atom in the WO_4 tetrahedron is shared with three tin atoms, whereas the other three oxygens bridge to one tin atom each.

The recent applicative interest in tin tungstate is caused by its possible use in day-light photocatalysis [5, 7–10] and gas sensors [11, 12]. It was found that β - SnWO_4 exhibits high visible-light photocatalytic activity in both microcrystalline ($d \sim 1 \mu\text{m}$) and nanocrystalline ($d < 20$ nm) forms [5, 9, 10]. The photocatalytic performance of nanocrystalline α - SnWO_4 can be enhanced by Zn^{2+} doping, inducing band gap narrowing [13].

The photocatalytic activity of two tin tungstate phases is strongly related to their small band gaps (indirect $E_g = 1.64$ eV in α - SnWO_4 [5] and direct $E_g = 2.6$ – 2.7 eV in β - SnWO_4 [5, 9, 10]) and their unique band structures [1]. Results of density functional theory (DFT) calculation [5] suggest that the valence band in both tungstates is mainly composed of strongly interacting O 2p and Sn 5s states, whereas the conduction band has a W 5d–O 2p antibonding character with an admixture of Sn 5p states.

0031-8949/14/044005-05\$33.00

© 2014 The Royal Swedish Academy of Sciences. Printed in the UK



Paldies par uzmanību !